

General Description

The MY10N80D is silicon N-CH Enhanced VDMOSFETS is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

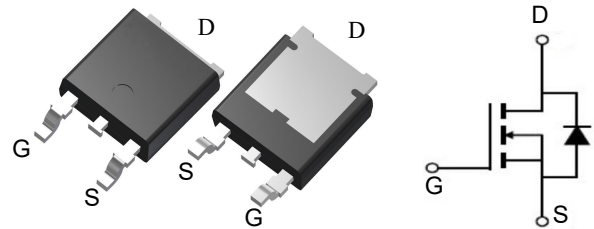


Features

V_{DSS}	800	V
I_D	10	A
$P_D(T_C=25^{\circ}C)$	125	W
$R_{DS(ON)}(at V_{GS}=10V)$	410	$m\Omega$

Application

- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)
- Switch Mode Power Supply (SMPS)



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY10N80D	TO-252-2L	MY10N80D	2500

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DS}	800	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current (note1)	I_{DM}	18	A
Gate Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	198	mJ
Avalanche Current (note1)	I_{AR}	3.5	A
Repetitive Avalanche Energy (note1)	E_{AR}	14	mJ
Power Dissipation ($T_C = 25^{\circ}C$)	P_D	125	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^{\circ}C$
Thermal Resistance, Junction-to-Case	R_{thJC}	1.0	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	$^{\circ}C/W$

MY10N80D

800V N-Channel Enhancement Mode MOSFET



Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Type	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_J = 25^{\circ}\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4.0A$	--	410	500	m Ω
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$	--	611	--	pF
Output Capacitance	C_{oss}		--	18	--	
Reverse Transfer Capacitance	C_{rss}		--	0.9	--	
Total Gate Charge	Q_g	$V_{DD} = 520V, I_D = 4.0A,$ $V_{GS} = 10V$	--	17.7	--	nC
Gate-Source Charge	Q_{gs}		--	2.8	--	
Gate-Drain Charge	Q_{gd}		--	6.1	--	
Turn-on Delay Time	$T_d(on)$	$V_{DD} = 400V, I_D = 4.0A,$ $R_G = 25\text{ }\Omega$	--	10	--	ns
Turn-on Rise Time	T_r		--	33	--	
Turn-off Delay Time	$T_d(off)$		--	30	--	
Turn-off Fall Time	T_f		--	28	--	
Continuous Body Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$	--	--	6	A
Pulsed Diode Forward Current	I_{SM}		--	--	18	
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 4.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 4.0A,$ $di_F/dt = 100A/\mu s$	--	248	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.4	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 4A, V_{DD} = 50V, R_G = 25\text{ }\Omega$, Starting $T_J = 25\text{ }^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics

Figure 1. Output Characteristics (T = 25°C)

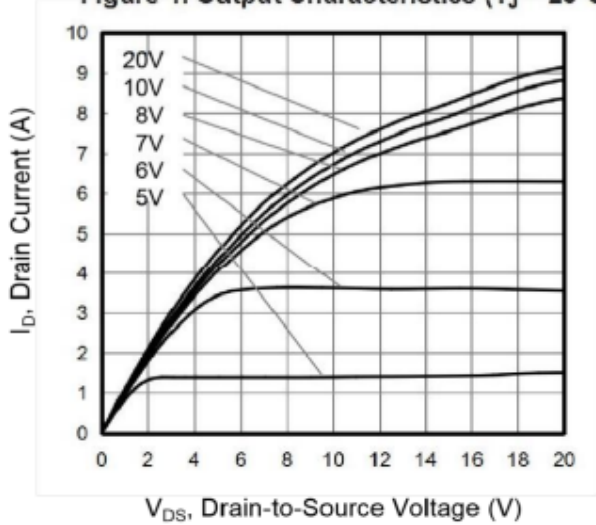


Figure 2. Body Diode Forward Voltage

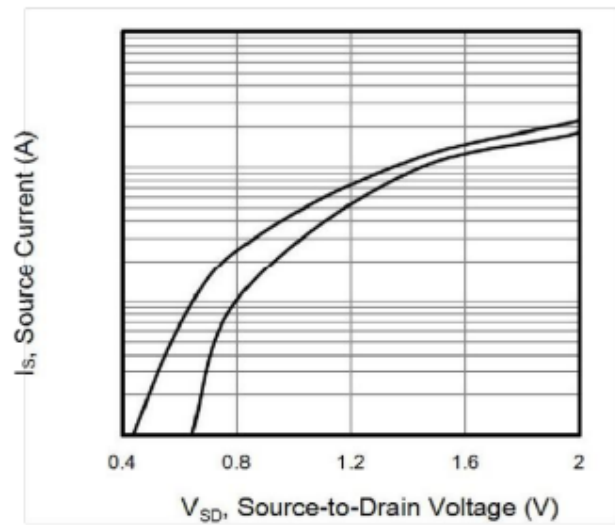


Figure 3. Drain Current vs. Temperature

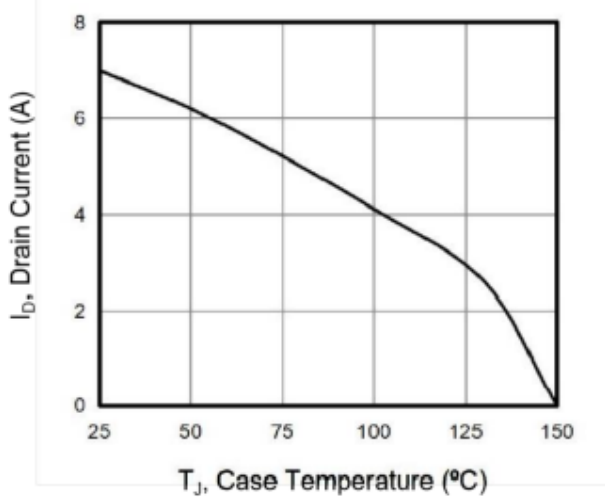


Figure 4. BV_DS Variation vs. Temperature

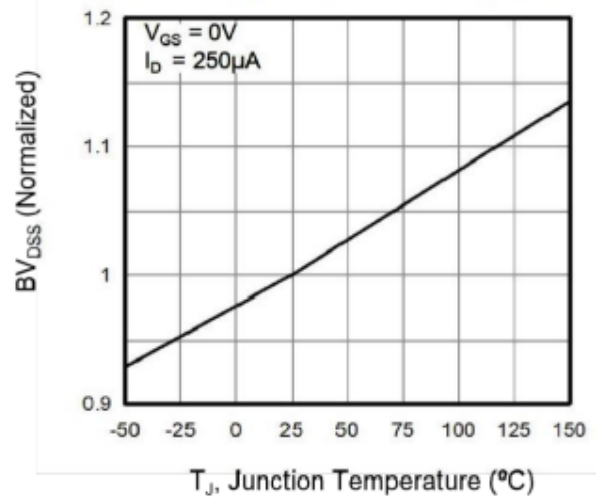


Figure 5. Transfer Characteristics

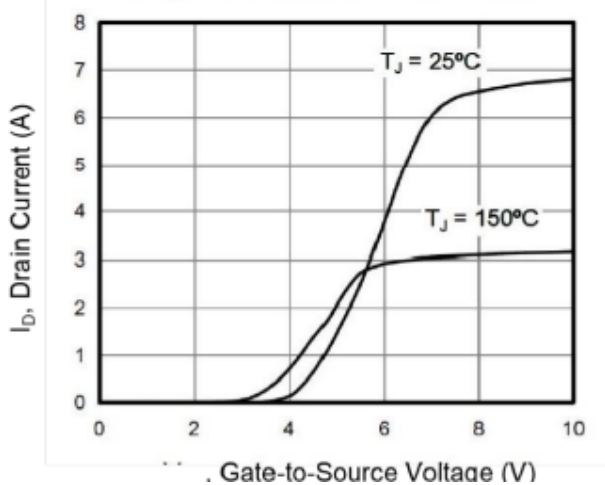


Figure 6. On-Resistance vs. Temperature

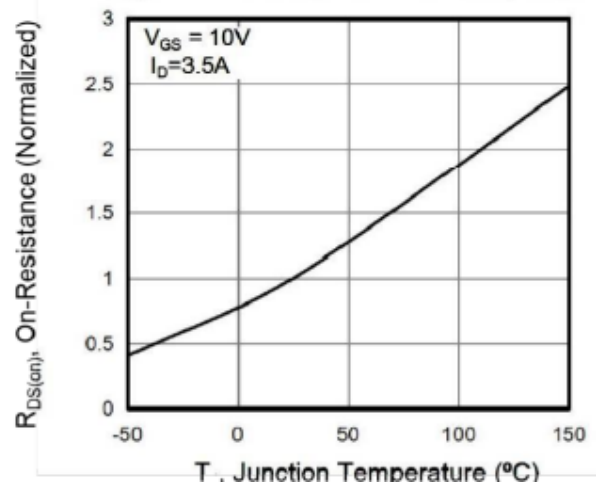


Figure 7. Capacitance

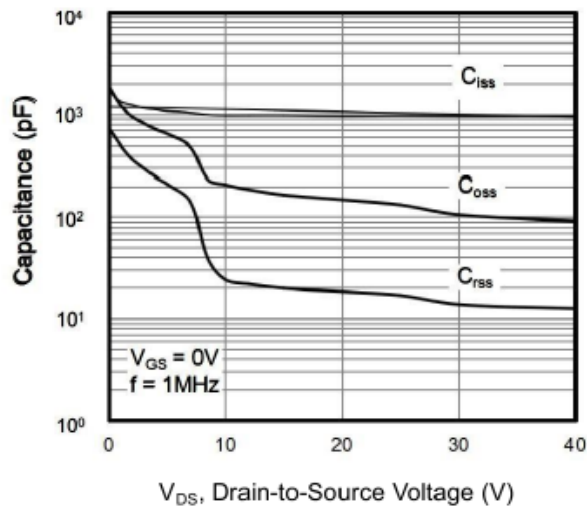


Figure 8. Gate Charge

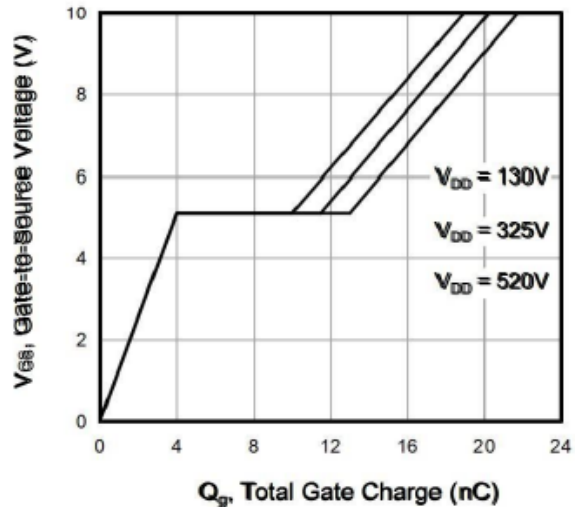


Figure 9. Transient Thermal Impedance

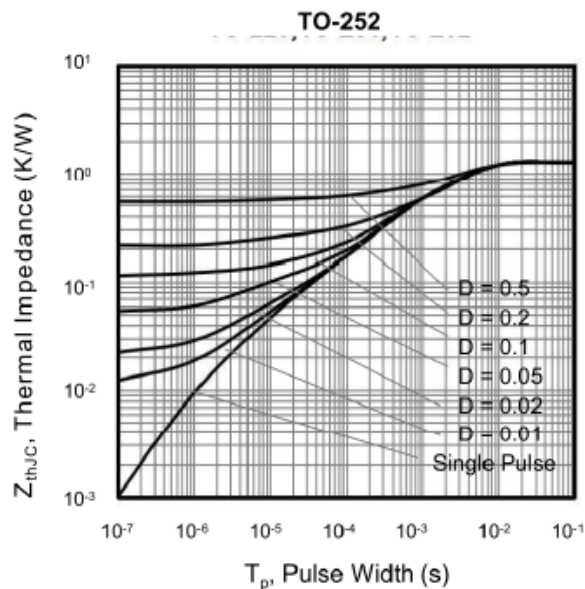


Figure 10. Transient Thermal Impedance

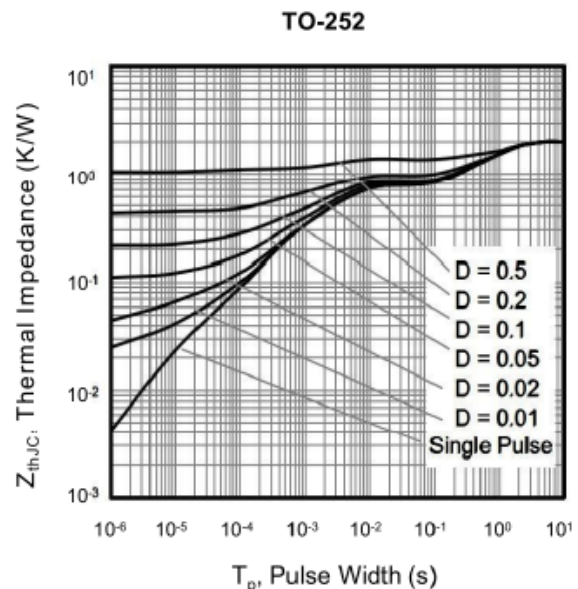
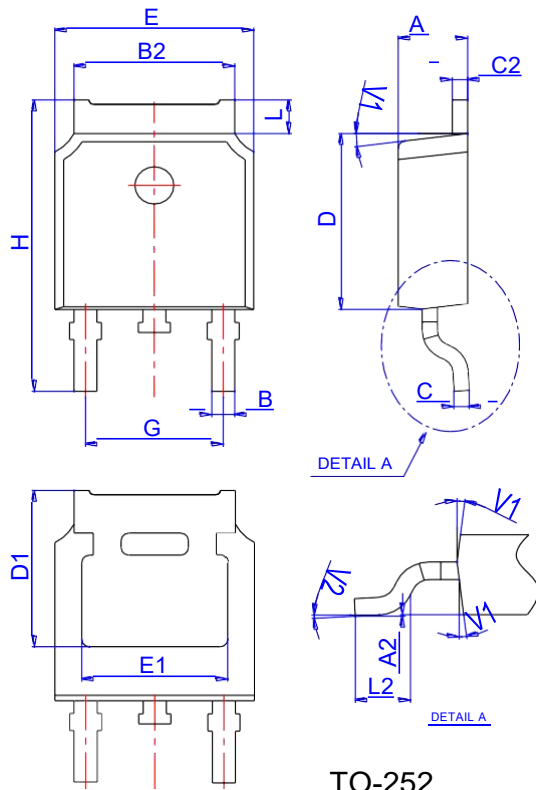


Figure A: Gate Charge Test Circuit and Waveform

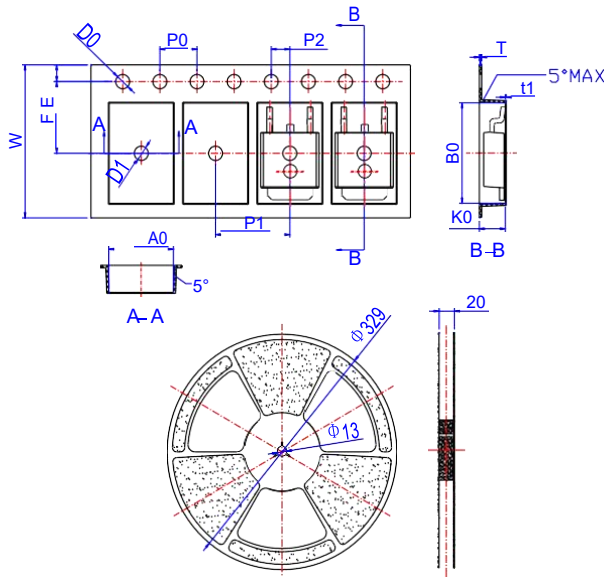
Package Mechanical Data-TO-252-JQ Single



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583